

ABSTRACT

A slurry for chemical mechanical polishing (CMP) of a copper or silver containing film provides at least one reactant for reacting with the copper or silver film to form a soft layer on the surface of the copper or silver film. The soft layer has a hardness less than the copper or silver film. The slurry preferably includes 5 either no particles or particles which are softer than the copper or silver layer. A method for chemical mechanical polishing (CMP) a copper or silver containing film includes the steps of providing a slurry for reacting with the copper or silver film to form a soft layer on the surface of the copper or silver film and uses either no particles or particles softer than the copper or silver film, applying the slurry to the 10 copper or silver film to form the soft layer, and removing the soft layer using a polishing pad.